

Dual P-Channel MOSFET

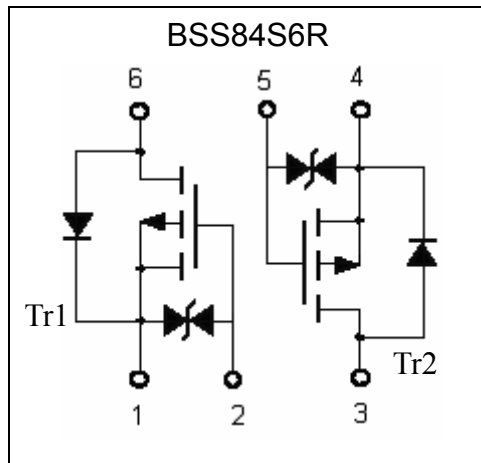
BSS84S6R

| | |
|------------------------------------|------------------|
| BV_{DSS} | -50V |
| I_D | -170mA |
| $R_{DSON}@V_{GS}=-10V, I_D=-100mA$ | 5 Ω (typ) |
| $R_{DSON}@V_{GS}=-5V, I_D=-100mA$ | 6 Ω (typ) |
| $R_{DSON}@V_{GS}=-3V, I_D=-30mA$ | 8 Ω (typ) |

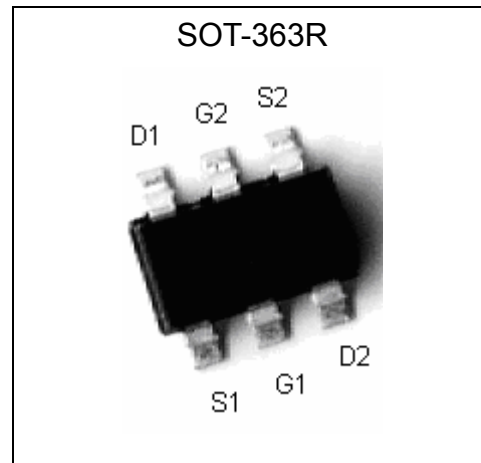
Features

- Low on-resistance
- High ESD capability
- High speed switching
- Low-voltage drive(-2.5V)
- Pb-free package

Equivalent Circuit



Outline



The following characteristics apply to both Tr1 and Tr2

Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit | |
|--|----------------|------------------|------------|----|
| Drain-Source Voltage | V_{DS} | -50 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current @ $T_A=25^\circ C, V_{GS}=-5V$ (Note 3) | I_D | -170 | mA | |
| Continuous Drain Current @ $T_A=85^\circ C, V_{GS}=-5V$ (Note 3) | | -120 | | |
| Pulsed Drain Current (Notes 1, 2) | I_{DM} | -800 | mA | |
| Maximum Power Dissipation (Note 3) | P_D | $T_A=25^\circ C$ | 300 | mW |
| | | $T_A=85^\circ C$ | 160 | |
| Operating Junction and Storage Temperature | T_j, T_{stg} | -55~+150 | $^\circ C$ | |

- Note : 1. Pulse width limited by maximum junction temperature.
 2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 3. Surface mounted on 1 in² copper pad of FR-4 board, $t \leq 5s$.



Thermal Performance

| Parameter | Symbol | Limit | Unit |
|---|--------|-------|------|
| Thermal Resistance, Junction-to-Ambient(PCB mounted) (Note) | Rth,ja | 415 | °C/W |

Note : Surface mounted on 1 in² copper pad of FR-4 board, t≤5s.

Electrical Characteristics (Tj=25°C, unless otherwise noted)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---------------------------|------|-------|------|--|---|
| Static | | | | | |
| BV _{DSS} | -50 | - | - | V | V _{GS} =0, I _D =-250μA |
| V _{GS(th)} | -1 | -1.4 | -2 | V | V _{DS} =V _{GS} , I _D =-250μA |
| I _{GSS} | - | - | ±8 | μA | V _{GS} =±20V, V _{DS} =0 |
| I _{DSS} | - | - | 1 | | V _{DS} =50V, V _{GS} =0 |
| | - | - | 10 | V _{DS} =40V, V _{GS} =0 (Tj=70°C) | |
| *R _{DS(ON)} | - | 5 | 7 | Ω | V _{GS} =-10V, I _D =-100mA |
| | - | 6 | 8.5 | | V _{GS} =-5V, I _D =-100mA |
| | - | 8 | 12 | | V _{GS} =-3V, I _D =-30mA |
| *G _{FS} | 80 | - | - | mS | V _{DS} =-10V, I _D =-100mA |
| Dynamic | | | | | |
| C _{iss} | - | 24 | - | pF | V _{DS} =-25V, V _{GS} =0, f=1MHz |
| C _{oss} | - | 4.6 | - | | |
| C _{rss} | - | 1.5 | - | | |
| t _{d(ON)} | - | 2.7 | - | ns | V _{DS} =-25V, I _D =-100mA, V _{GS} =-5V, R _G =3.3Ω |
| t _r | - | 3.3 | - | | |
| t _{d(OFF)} | - | 7.4 | - | | |
| t _f | - | 5 | - | | |
| Q _g | - | 1.4 | - | nC | V _{DS} =-40V, I _D =-170mA, V _{GS} =-5V |
| Q _{gs} | - | 0.36 | - | | |
| Q _{gd} | - | 0.29 | - | | |
| Source-Drain Diode | | | | | |
| *V _{SD} | - | -0.85 | -1.2 | V | V _{GS} =0V, I _S =-130mA |

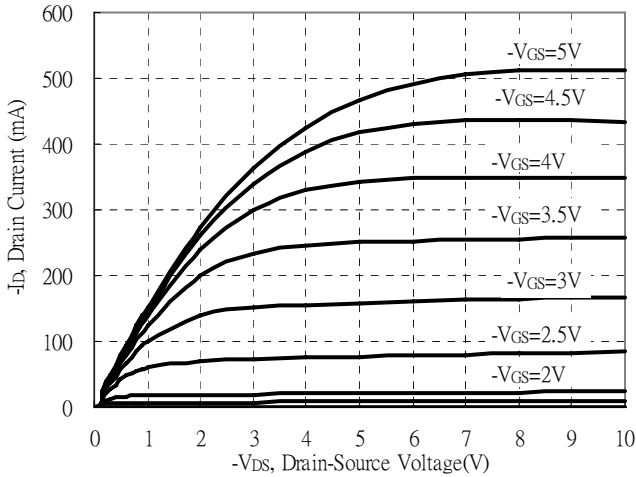
*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

Ordering Information

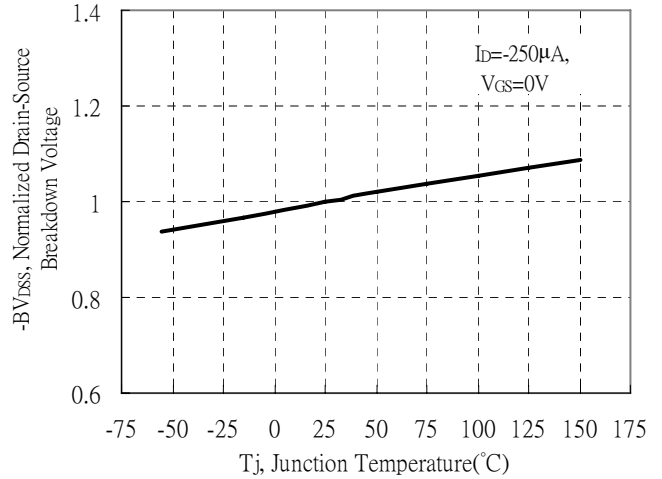
| Device | Package | Shipping |
|-----------------|--|------------------------|
| BSS84S6R-0-T1-G | SOT-363 (Pb-free lead plating and halogen-free package) | 3000 pcs / Tape & Reel |

Typical Characteristics

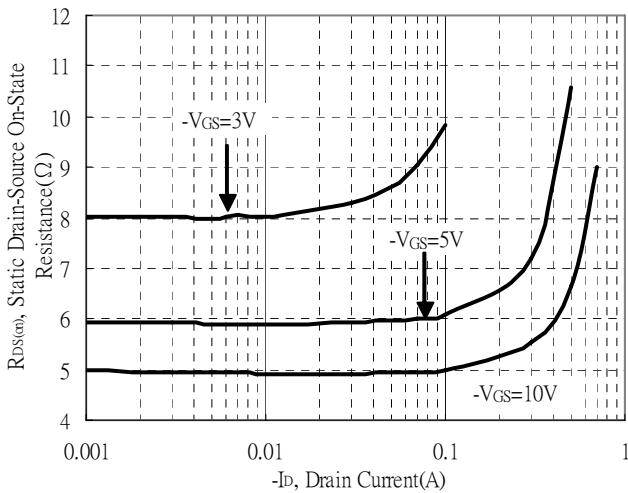
Typical Output Characteristics



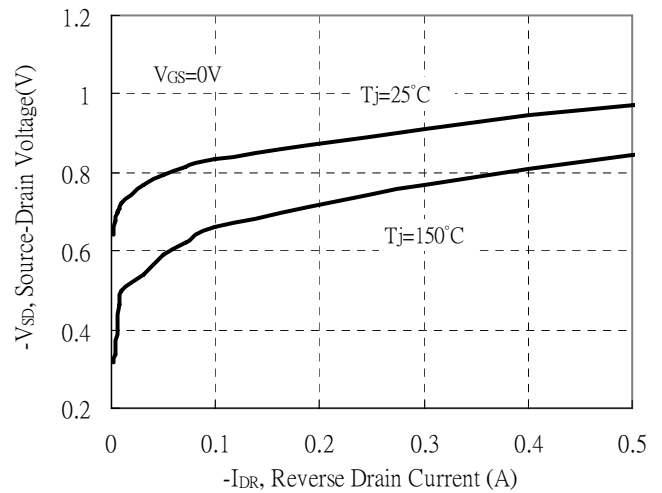
Breakdown Voltage vs Ambient Temperature



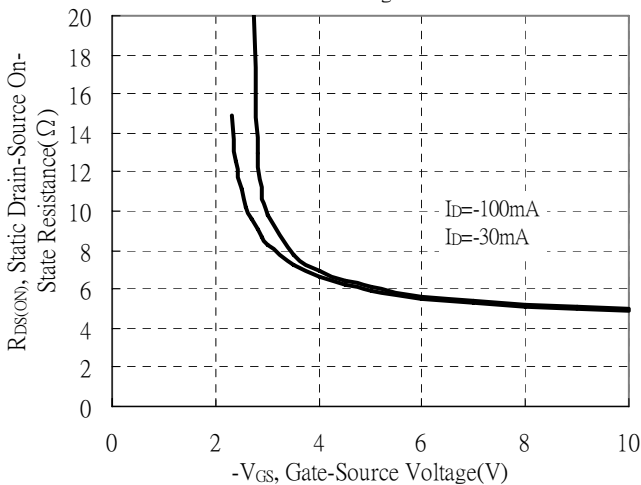
Static Drain-Source On-State resistance vs Drain Current



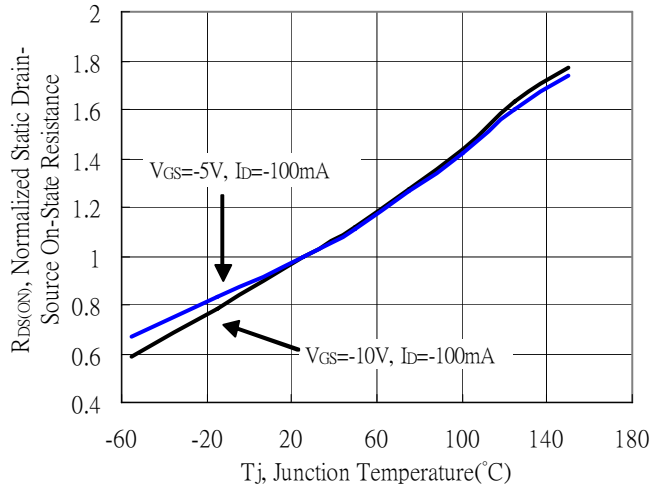
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

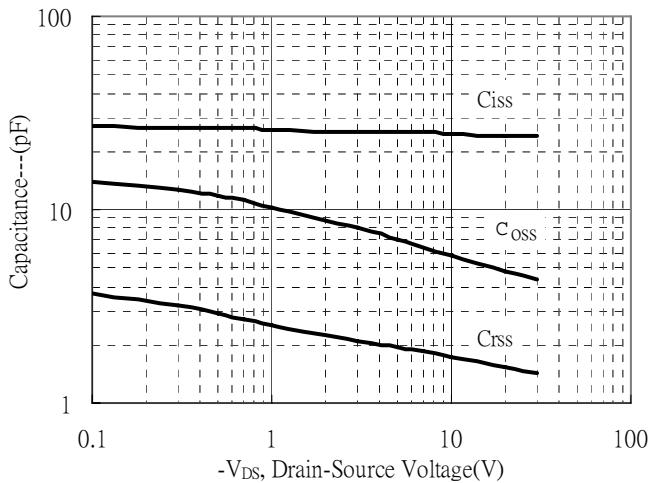


Drain-Source On-State Resistance vs Junction Temperature

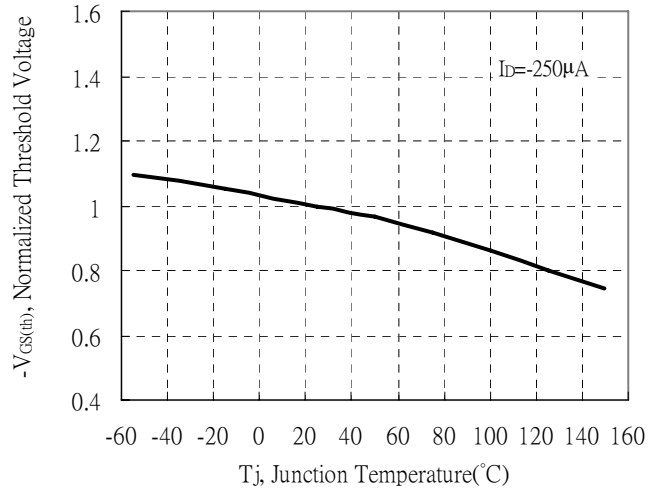


Typical Characteristics(Cont.)

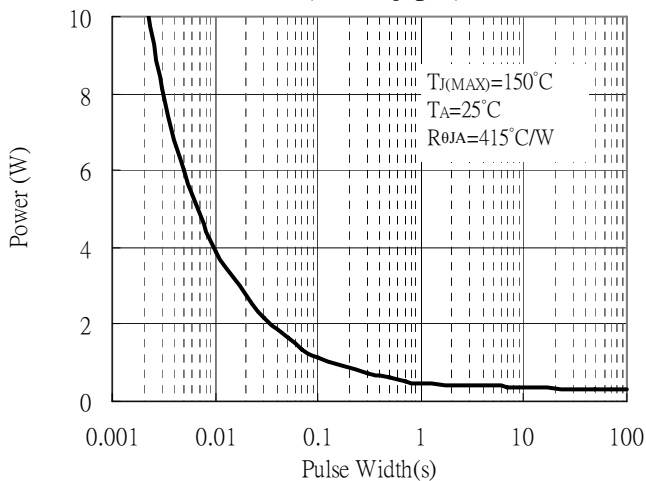
Capacitance vs Drain-to-Source Voltage



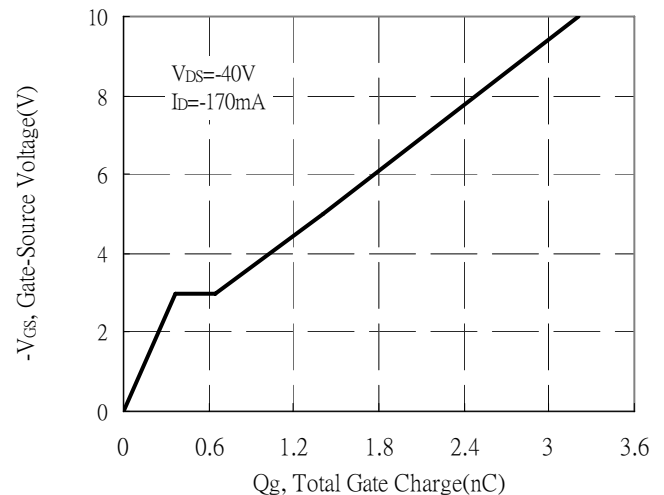
Threshold Voltage vs Junction Temperature



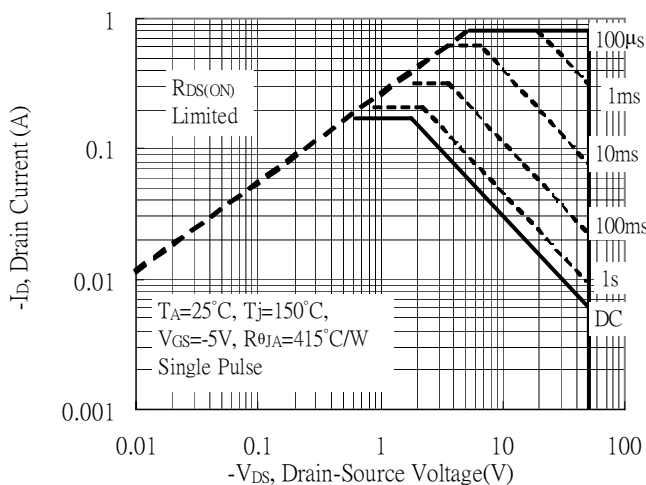
Single Pulse Power Rating, Junction to Ambient
 (Note on page 1)



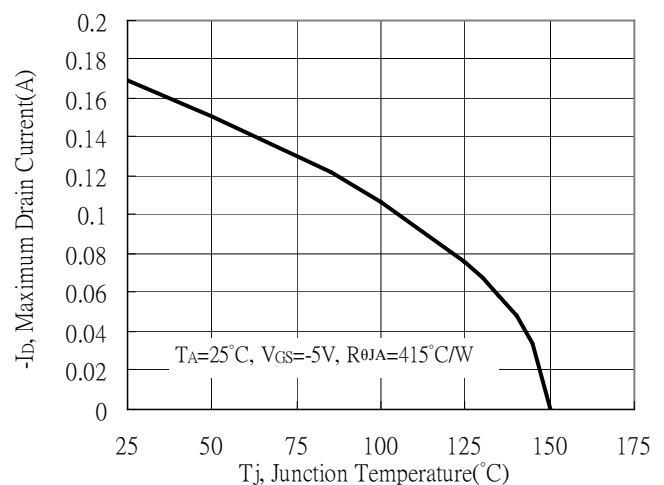
Gate Charge Characteristics



Maximum Safe Operating Area

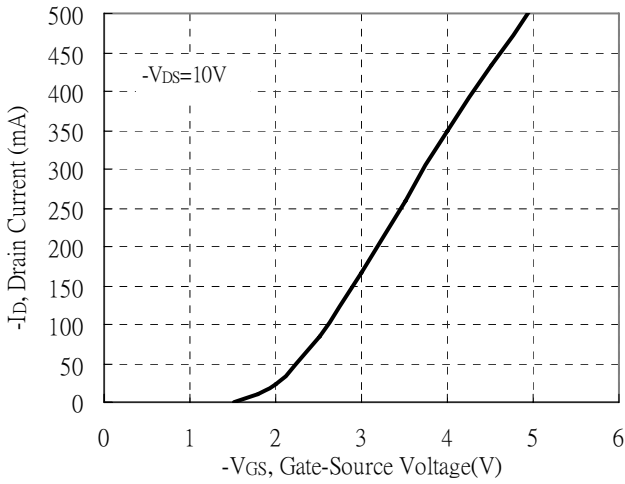


Maximum Drain Current vs Junction Temperature

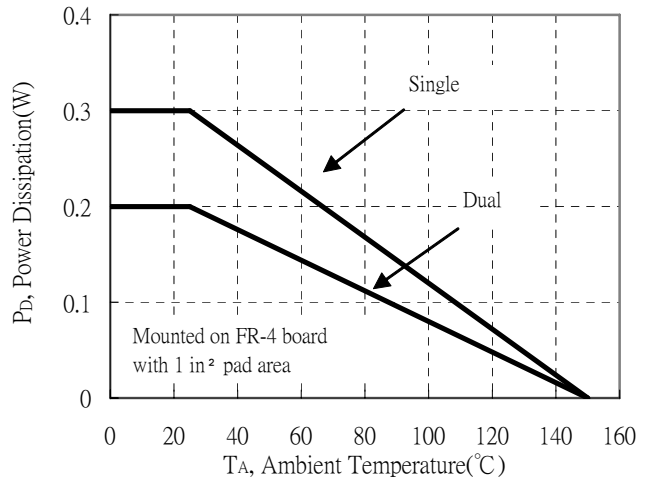


Typical Characteristics(Cont.)

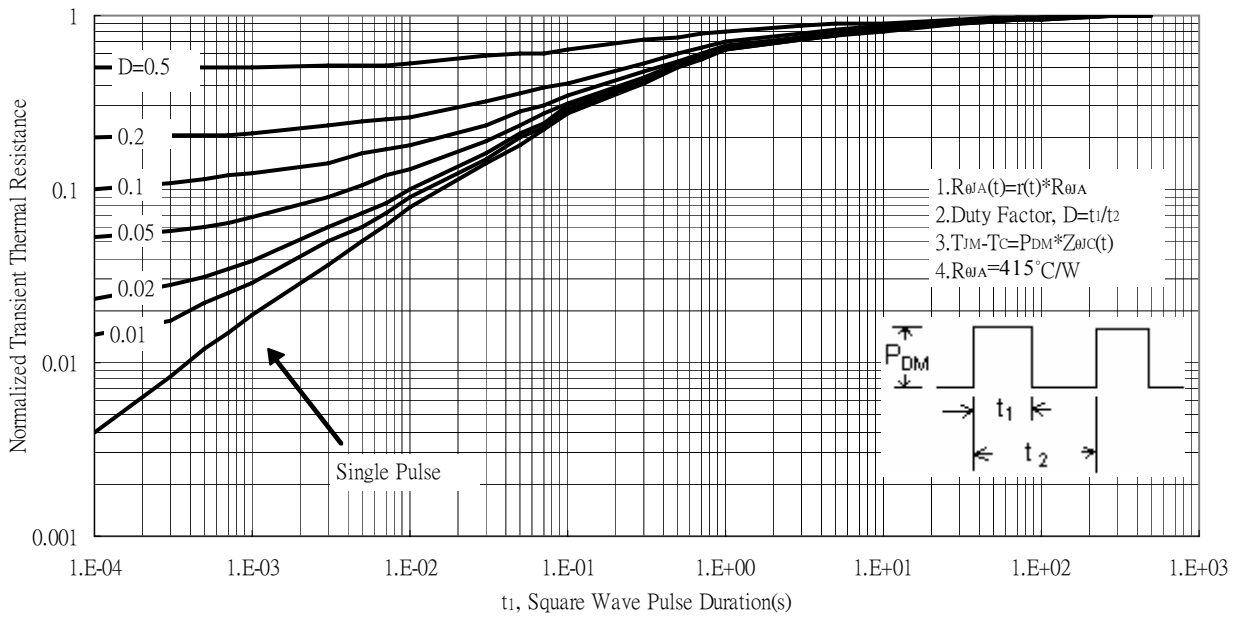
Typical Transfer Characteristics



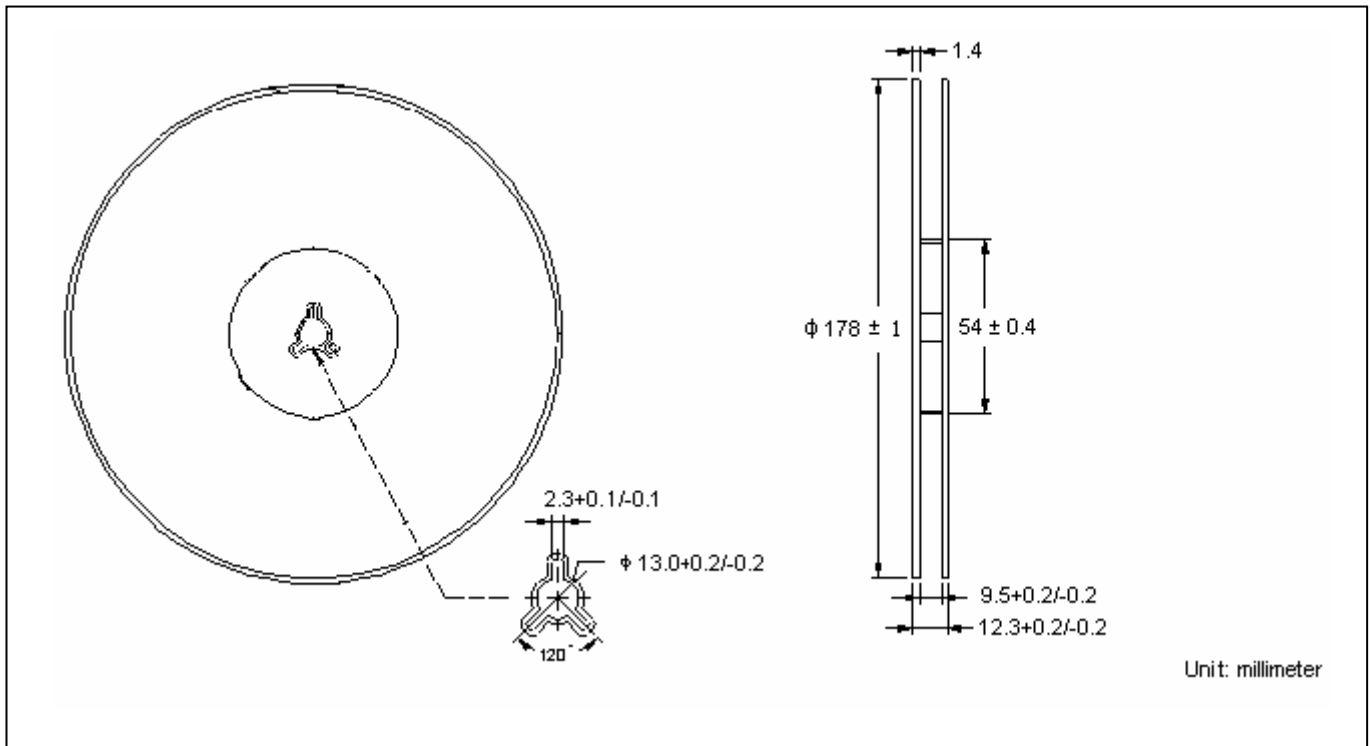
Power Derating Curves



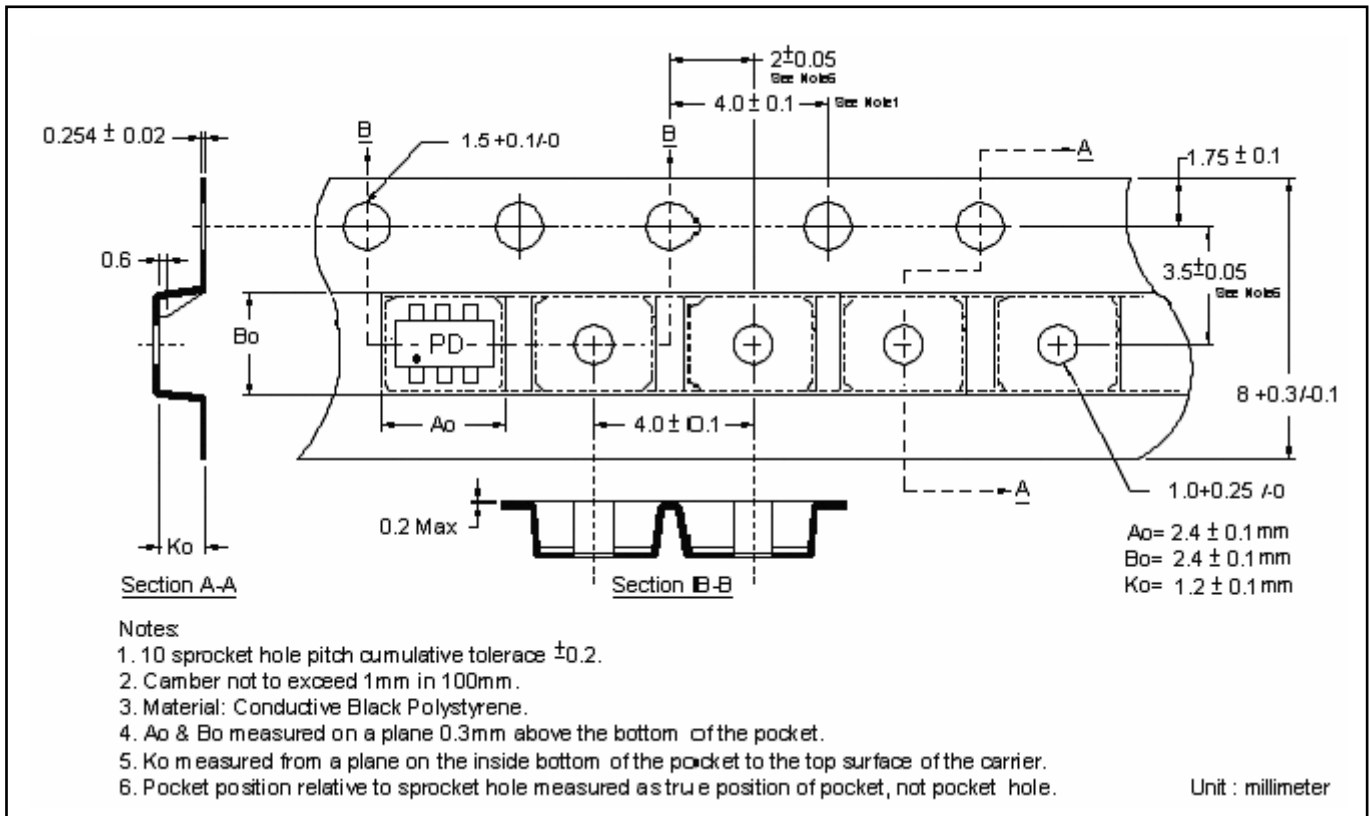
Transient Thermal Response Curves



Reel Dimension



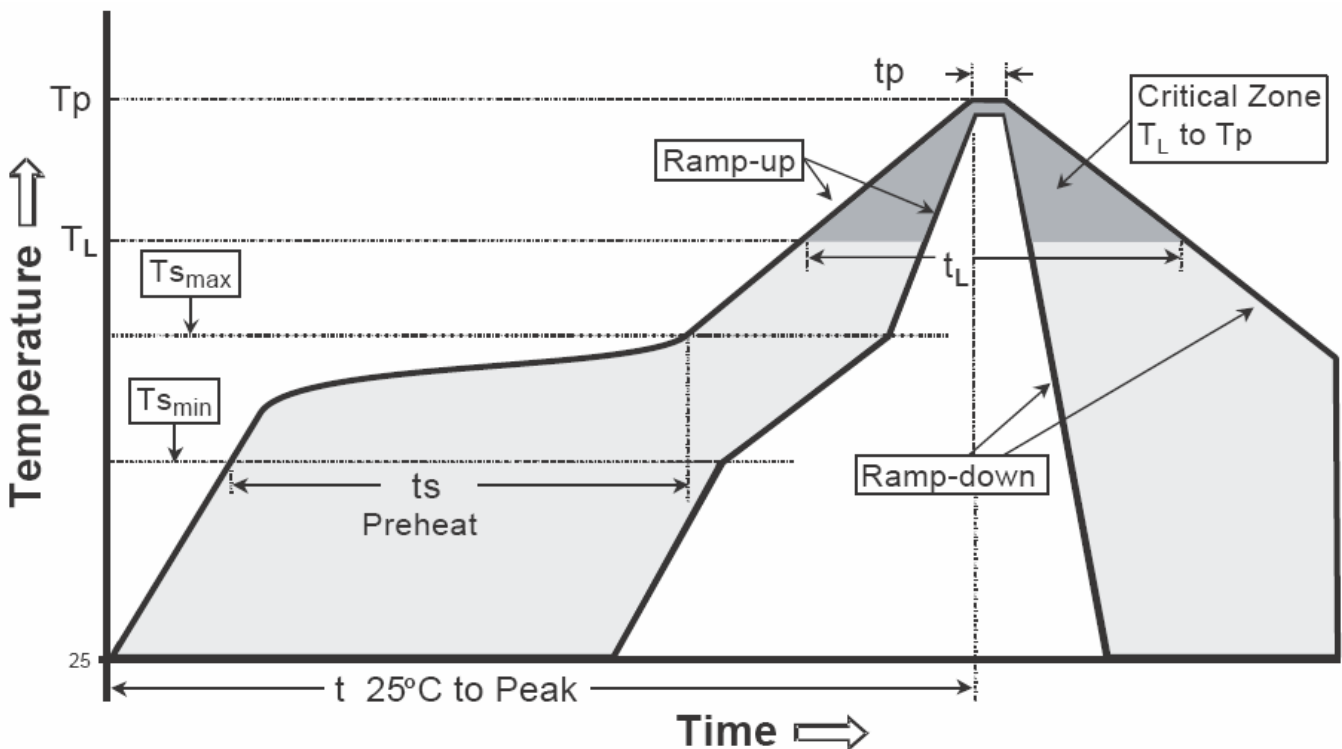
Carrier Tape Dimension



Recommended wave soldering condition

| | | |
|-----------------|------------------|-----------------|
| Product | Peak Temperature | Soldering Time |
| Pb-free devices | 260 +0/-5 °C | 5 +1/-1 seconds |

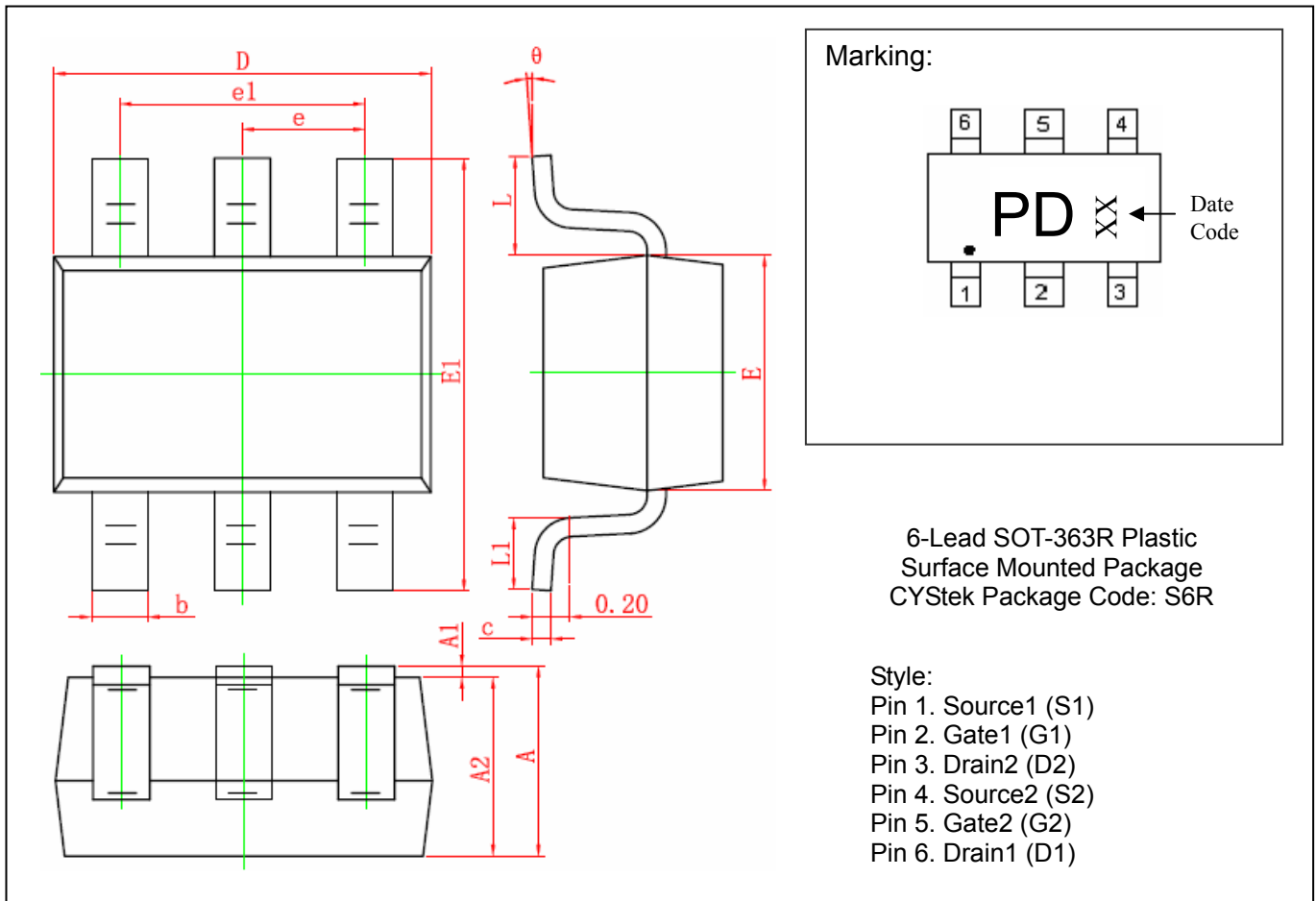
Recommended temperature profile for IR reflow



| Profile feature | Sn-Pb eutectic Assembly | Pb-free Assembly |
|---|-------------------------|------------------|
| Average ramp-up rate (T _{smax} to T _p) | 3°C/second max. | 3°C/second max. |
| Preheat | | |
| -Temperature Min(T _{s min}) | 100°C | 150°C |
| -Temperature Max(T _{s max}) | 150°C | 200°C |
| -Time(t _{s min} to t _{s max}) | 60-120 seconds | 60-180 seconds |
| Time maintained above: | | |
| -Temperature (T _L) | 183°C | 217°C |
| - Time (t _L) | 60-150 seconds | 60-150 seconds |
| Peak Temperature(T _P) | 240 +0/-5 °C | 260 +0/-5 °C |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds | 20-40 seconds |
| Ramp down rate | 6°C/second max. | 6°C/second max. |
| Time 25 °C to peak temperature | 6 minutes max. | 8 minutes max. |

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-363 Dimension



| DIM | Millimeters | | Inches | | DIM | Millimeters | | Inches | |
|-----|-------------|-------|--------|-------|-----|-------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.100 | 0.035 | 0.043 | E1 | 2.150 | 2.450 | 0.085 | 0.096 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | e | 0.650 | TYP | 0.026 | TYP |
| A2 | 0.900 | 1.000 | 0.035 | 0.039 | e1 | 1.200 | 1.400 | 0.047 | 0.055 |
| b | 0.150 | 0.350 | 0.006 | 0.014 | L | 0.525 | REF | 0.021 | REF |
| c | 0.080 | 0.150 | 0.003 | 0.006 | L1 | 0.260 | 0.460 | 0.010 | 0.018 |
| D | 2.000 | 2.200 | 0.079 | 0.087 | θ | 0° | 8° | 0° | 8° |
| E | 1.150 | 1.350 | 0.045 | 0.053 | | | | | |

Notes : 1.Controlling dimension : millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek **semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.**
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.